onsemi

MARKING DIAGRAMS 8888 XXXX US8 ALYW **US SUFFIX CASE 493** ᆸᆸᆸᇉ Commercial UDFN8, 1.95x1.0 **MU1 SUFFIX** ХМ CASE 517CA UDFN8, 1.6x1.0 ΧM **MU2 SUFFIX** CASE 517BY o 1 UDFN8, 1.45x1.0 **MU3 SUFFIX** ΧМ CASE 517BZ UQFN8, 1.6x1.6 MQ1 SUFFIX XX M= CASE 523AN UQFN8, 1.4x1.2 XM MQ2 SUFFIX CASE 523AS 10 X, XX, XXXX = Specific Device Code = Assembly Location А L = Lot Code Y = Year Code

W

Μ

ORDERING INFORMATION

= Week Code

= Date Code = Pb-Free Package

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.



NL27WZ02

The NL27WZ02 is a high performance dual 2-input NOR Gate operating from a 1.65 V to 5.5 V supply.

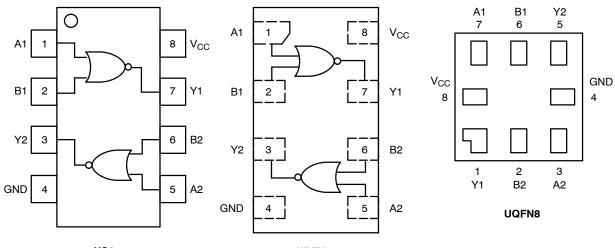
Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.5 ns t_{PD} at V_{CC} = 5 V (typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- IOFF Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in US8, UDFN8 and UQFN8 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Figure 1. Logic Symbol

NL27WZ02



US8

UDFN8

Figure 2. Pinout

PIN ASSIGNMENT (US8 / UDFN8)

Pin	Function
1	A1
2	B1
3	Y2
4	GND
5	A2
6	B2
7	Y1
8	V _{CC}

PIN ASSIGNMENT (UQFN8)

	· · ·
Pin	Function
1	Y1
2	B2
3	A2
4	GND
5	Y2
6	B1
7	A1
8	V _{CC}

FUNCTION TABLE

Inp	Output	
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

H = HIGH Logic Level L = LOW Logic Level

MAXIMUM RATINGS

Symbol	Charae	cteristics	Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
	DC Output Voltage	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
IOUT	DC Output Source/Sink Current	±50	mA	
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or G	Bround Pin	±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for	r 10 secs	260	°C
ТJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)	US8 UQFN8 UDFN8	250 210 231	°C/W
PD	Power Dissipation in Still Air	US8 UQFN8 UDFN8	500 595 541	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Applicable to devices with outputs that may be tri-stated.

 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A. 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}		Mode (High or Low State) Tri-State Mode (Note 1) r-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	$\begin{array}{l} V_{CC} = 1.65 \; V \; to \; 1.95 \; V \\ V_{CC} = 2.3 \; V \; to \; 2.7 \; V \\ V_{CC} = 3.0 \; V \; to \; 3.6 \; V \\ V_{CC} = 4.5 \; V \; to \; 5.5 \; V \end{array}$	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	Τ ₄	م = 25°	c	–55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Мах	Units
VIH	High-Level Input		1.65 to 1.95	$0.75 \times V_{CC}$			$0.75 \times V_{CC}$		V
	Voltage (NLV)		2.3 to 5.5	0.70 x V _{CC}			$0.70 \times V_{CC}$		
	High-Level Input		1.65 to 1.95	$0.65 \times V_{CC}$			0.65 x V _{CC}		V
	Voltage		2.3 to 5.5	0.70 x V _{CC}			$0.70 \times V_{CC}$		1
V _{IL}	Low-Level Input		1.65 to 1.95			0.25 x V _{CC}		0.25 x V _{CC}	V
	Voltage (NLV)		2.3 to 5.5			0.30 x V _{CC}		0.30 x V _{CC}	1
	Low-Level Input		1.65 to 1.95			0.35 x V _{CC}		0.35 x V _{CC}	V
	Voltage		2.3 to 5.5			0.30 x V _{CC}		0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage	$ \begin{array}{l} V_{IN} = V_{IH} \mbox{ or } V_{IL} \\ I_{OH} = -100 \ \mu A \\ I_{OH} = -4 \ m A \\ I_{OH} = -8 \ m A \\ I_{OH} = -12 \ m A \\ I_{OH} = -16 \ m A \\ I_{OH} = -24 \ m A \\ I_{OH} = -32 \ m A \end{array} $	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0	- - - - - -	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - - -	V
V _{OL}	Low-Level Output Voltage		1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55	- - - - -	0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	1.65 to 5.5	-	-	±0.1	-	±1.0	μA
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	I	1.0	_	10	μA
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	-	I	1.0	_	10	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

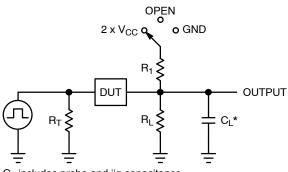
AC ELECTRICAL CHARACTERISTICS

				T _A = 25°C		T _A = −55 to 125°C			
Symbol	Parameter	V _{CC} (V)	Test Conditions	Min	Тур	Max	Min	Max	Units
t _{PLH} , Propagation Delay,	1.65 to 1.95	C _L = 15 pF	-	7.4	9.5	-	9.7	ns	
^T PHL	t _{PHL} (A or B) to Y	2.3 to 2.7	$R_L = 1 M\Omega$ $R_1 = Open$	-	3.3	5.4	-	5.8	
		3.0 to 3.6		-	2.6	3.9	-	4.3	
		4.5 to 5.5		-	1.9	3.1	-	3.3	
		3.0 to 3.6	$C_{L} = 50 \text{ pF},$	-	3.2	4.8	-	5.2	
		4.5 to 5.5	$R_L = 500 \Omega$, $R_1 = Open$	_	2.5	3.7	-	4.0	

CAPACITIVE CHARACTERISTICS

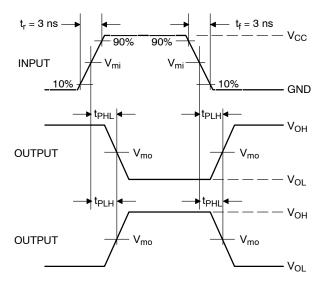
Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V _{CC} = 3.3 V, V _{IN} = 0 V or V _{CC} 10 MHz, V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	9 11	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit



Test	Switch Position	C _L , pF	R_{L}, Ω	R ₁ , Ω	
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table			
t _{PLZ} / t _{PZL}	$2 \times V_{CC}$	50	500	500	
t _{PHZ} / t _{PZH}	GND	50	500	500	
V Don't Cor					

X = Don't Care

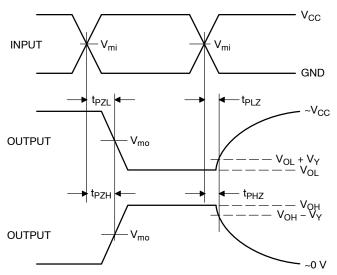


Figure 4. Switching Waveforms

		V _m o		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL27WZ02USG	US8	L3	Q4	3000 / Tape & Reel
NL27WZ02USG-L22190**	US8	L3	Q4	3000 / Tape & Reel
NL27WZ02MQ1TCG (In Development)	UQFN8, 1.6 x 1.6, 0.5P	TBD	TBD	3000 / Tape & Reel
NL27WZ02MU1TCG	UDFN8, 1.95 x 1.0, 0.5P	AL	Q4	3000 / Tape & Reel
NL27WZ02MU1TWG	UDFN8, 1.95 x 1.0, 0.5P	AM	Q1	3000 / Tape & Reel
NL27WZ02MU3TCG	UDFN8, 1.45 x 1.0, 0.35P	J	Q4	3000 / Tape & Reel
NL27WZ02MU2TCG	UDFN8, 1.6 x 1.0, 0.4P	AH	Q4	3000 / Tape & Reel
NL27WZ02MQ2TCG (In Development)	UQFN8, 1.4 x 1.2, 0.4P	TBD	TBD	3000 / Tape & Reel

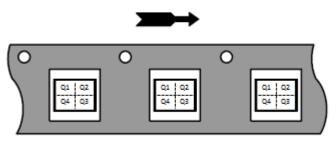
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

**Please refer to NLV specifications for this device.

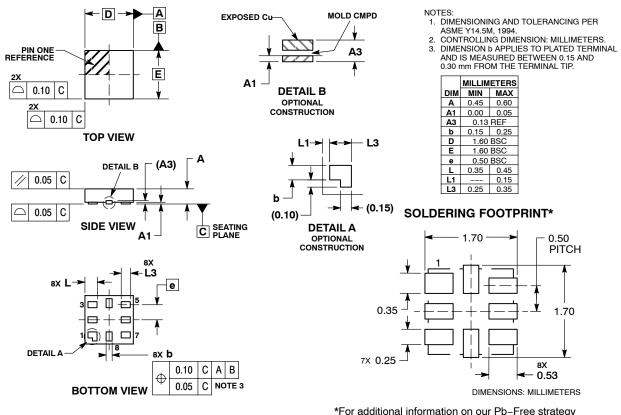
Pin 1 Orientation in Tape and Reel

Direction of Feed



PACKAGE DIMENSIONS

UQFN8, 1.6x1.6, 0.5P CASE 523AN ISSUE O

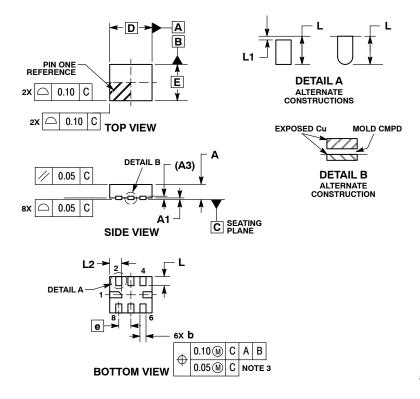


*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

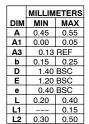
NL27WZ02

PACKAGE DIMENSIONS

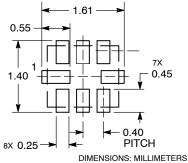
UQFN8, 1.4x1.2, 0.4P CASE 523AS **ISSUE A**



NOTES:
DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
CONTROLLING DIMENSION: MILLIMETERS.
DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25 mm FROM THE TERMINAL TIP.



SOLDERING FOOTPRINT*



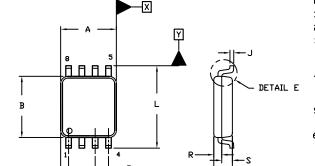
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DURSEM

DATE 01 SEP 2021



SCALE 4:1



-c

11

0.10 (0.004) T

١

DETAIL E

NOTES:

US8 **CASE 493 ISSUE F**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

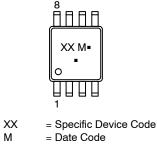
2. CONTROLLING DIMENSION: MILLIMETERS

R 0.10 TYP

- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION, З. OR GATE BURR. MOLD FLASH, PROTRUSION, OR GATE BURR SHALL NOT EXCEED 0.14 (0.0055') PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT 4. EXCEED 0.14 (0.0055") PER SIDE.
- LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 5. 0.0076-0.0203 MM (0.003-0.008").
- ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 MM (0.002"). 6.

	MILLIMETERS		INC	HES
DIM	MIN.	MAX.	MIN.	MAX.
A	1.90	2.10	0.075	0.083
В	2.20	2.40	0.087	0.094
С	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50	BSC	0.020	BSC
н	0.40	REF	0.016 REF	
J	0.10	0.18	0.004	0.007
к	0.00	0.10	0.000	0.004
L	3.00	3.25	0.118	0.128
м	0*	6*	0*	6*
N	0*	10*	0*	10*
Р	0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
V	0.12	BSC	0.005	BSC

GENERIC **MARKING DIAGRAM***



= Pb-Free Package

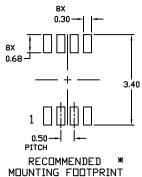
(Note: Microdot may be in either location)

Μ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON04475D Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	US8		PAGE 1 OF 1		
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.					

- G P SEATING PLANE n 甶 ⊕0.10 (0.004) ₩ T X Y

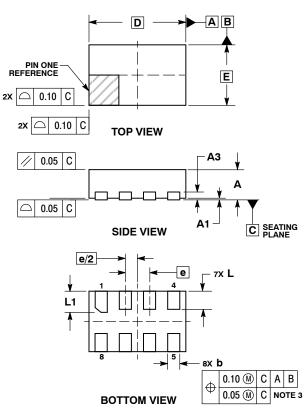


nal Infor

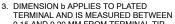




SCALE 4:1



NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.



BOTTIO AND MOLD T					
	MILLIMETERS				
DIM	MIN	MAX			
Α	0.45	0.55			
A1	0.00	0.05			
A3	0.13 REF				
b	0.15	0.25			
D	1.60 BSC				
Е	1.00 BSC				
е	0.40 BSC				
L	0.25	0.35			
L1	0.30	0.40			

GENERIC **MARKING DIAGRAM***

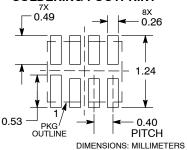


X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " .", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*

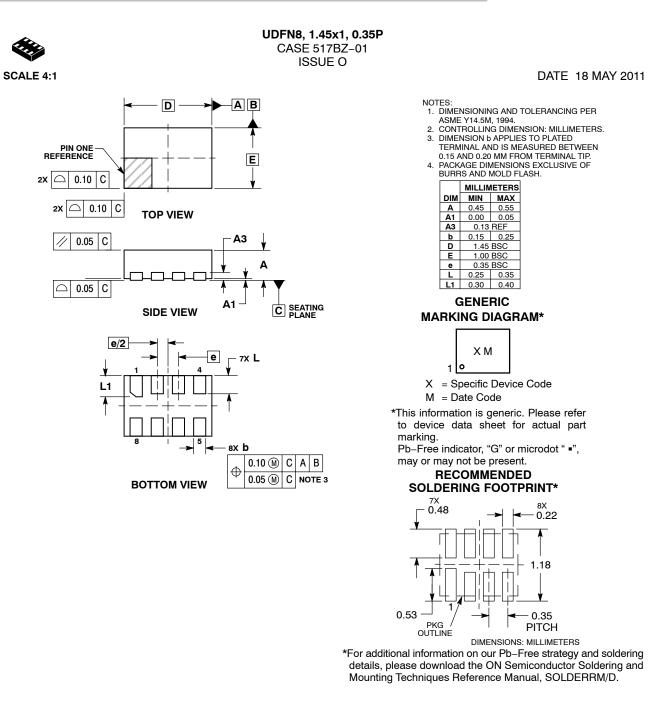


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON56788E Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	UDFN8, 1.6X1, 0.4P		PAGE 1 OF 1		
ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.					

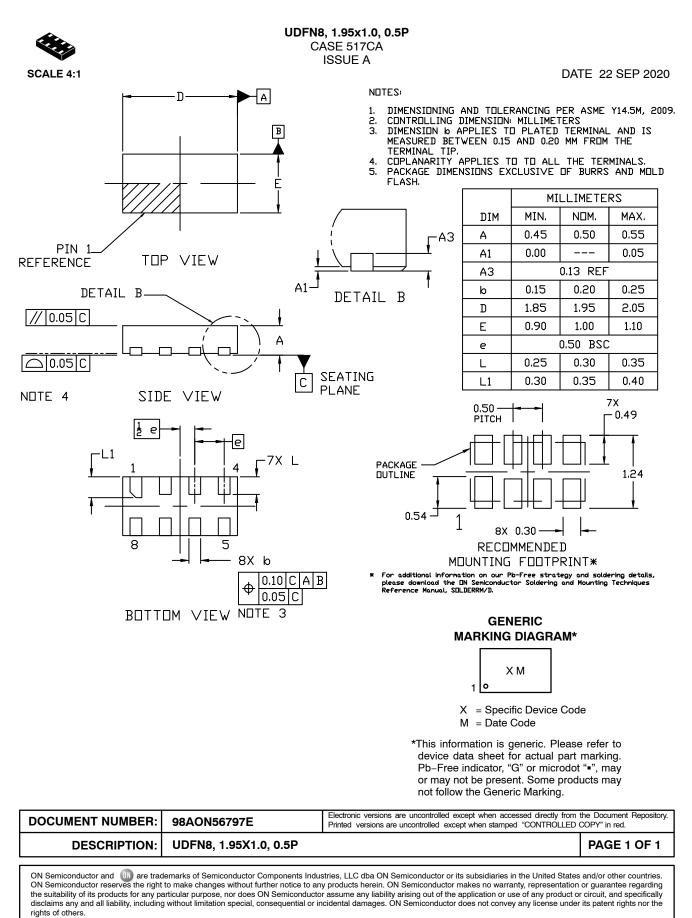
UDFN8, 1.6x1, 0.4P CASE 517BY-01 ISSUE O





DOCUMENT NUMBER:	98AON56796E	Electronic versions are uncontrolled except when accessed directly from the Printed versions are uncontrolled except when stamped "CONTROLLED (
DESCRIPTION:	UDFN8, 1.45X1, 0.35P		PAGE 1 OF 1		
ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights or the					





onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative